Impurity-induced step patterns in vapor and solution growth: From step bunches to Supersteps

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- Change in Morphology, step flow rate on the crystal surface Recent Examples: Mg in Calcite growth, Fe in KDP (KH<sub>2</sub>PO<sub>4</sub>)
- Impurities can serve as nucleation sites Acceleration of Calcite Kinetics by Abalone Nacre Proteins
- Change bulk properties of the crystal Impurities in KDP crystals can dramatically affect laser properties

We focus on impurities that inhibit step motion

# Simple Langmuir description of impurity adsorption $\frac{dc_i}{dt} = F_i(1-c_i) - \varepsilon_i c_i = F_i - (\varepsilon_i + F_i)c_i$ $\overline{c_i} = \frac{F_i}{\varepsilon_i + F_i}$ $c_i(t) = \overline{c_i}(1 - e^{-(\varepsilon_i + F_i)t})$ Filling time $\tau_i = (\varepsilon_i + F_i)^{-1}$

Impurities impede local step motion but are covered (or dislodged) by advancing step



Experiments on KH<sub>2</sub>PO<sub>4</sub> (KDP) crystals grown in solution (stirred) T.A. Land, T.L. Martin, G.T.R. Palmore, S.Potapenko and J.J. De Yoreo Nature, **399**, 442 (1999)

Small amount of Fe, Al, Cr impurities can completely stop growth of crystal.

Recovery occurs by motion of large bunches of steps (10-30steps) called **macrosteps** 

With Cr(III) and Al(III), **supersteps** (40-100 steps)

Phys. Rev. Lett. **93**, 216130 (2004)

Impurities embedded





#### Macrostep motion





Step face angle



Velocity of a step bunch proportional to the number of steps in the bunch. This is only valid for a small range of supersaturations Superstep and macrostep bunches move together

## Frank Model - 1958



Dynamics of impurity adsorption drives bunching

1-D model, no curvature effects, step repulsions ignored (no overhangs permitted) Growth slows down as bunches form and more impurities are adsorbed

# Cabrera-Vermilea (CV) Model - 1958



1. Impurities stick on surface

- 2. If impurities are far apart on average step can squeeze between them
- 3. If impurities are too close to each other, they pin steps and stop motion

When critical nucleus  $\rho_c > d/2$  step pinned

$$\rho_c = \frac{\gamma \Omega}{kT \ln(1+\sigma)}$$

Step velocity as a function of supersaturation and impurity concentration has threshold:

$$v = 0 \qquad \qquad \sigma < \sigma_{th}$$
$$v = v_0 \left(1 - \frac{2\rho_c}{d}\right)^{1/2} \qquad \qquad \sigma > \sigma_{th}$$

Pinning related to impurity spacing through curvature;  $v_0$  is growth rate in absence of impurities

## New mesoscopic 2-D Monte-Carlo Model

- Generalization of Kandel-Weeks model (1994); Combines ideas from Frank and CV models
- Main component growth treated effectively like simplest BCF model with diffusion length  $l_d$
- Impurity treated as discrete particles on a square lattice with spacing a<sub>i</sub>
- Impurity flux  $F_i$  to unoccupied sites; evaporate from the surface with rate  $1/\tau_i$

- Covered impurity removed
- Impurity profile between steps





## New Model- Monte Carlo Scheme

- 1. Impurity sweep
- Step flow sweep Attempt to move step segments of length a<sub>i</sub> with an acceptance-rejection criteria based on Metropolis scheme.
- 3. Energy is due to line-tension, step repulsions, and extra impurity energy penalty  $E_i$  if step tries to cover impurity

$$E(\{X_n\}) = \sum_{y,n} \left[ \gamma (X_n(y+1) - X_n(y))^2 + \sum_{n'} G\left(\frac{1}{(X_n(y) - X_{n'}(y))^2}\right) \right]$$

$$P_{Trial-Backward} = \frac{1-A}{2} \qquad P_{Trial-Forward} = \frac{1+A}{2} - A \exp\left(-\frac{W}{l_d}\right)$$
$$P_{acc} = \min\left[1, \exp\left(-\frac{\Delta E + E_i}{kT}\right)\right] \qquad \text{in presence of impurity}$$

Negative curvature (like CV model) and repulsive force from step behind increases probability of forward move; Impurity decreases probability Diffusion length important in vapor growth of pure component



Solution growth: step velocity independent of terrace width



Bunch once formed can stay together!

 $l_d = 10$  A = 0.15 (moderate)  $\gamma = 0.5$  (moderate); [F<sub>i</sub>=0.00001  $\epsilon_i$ =0.00004 E<sub>i</sub>=4.5 G=1 for all]

 $l_d = 10$  A = 0.9 (very large)  $\gamma = 0.1$  (Low Line Tension)

## Observations from these results for vapor growth

- 1. Bunching occurs with initial pairing, followed by slow coarsening
- 2. Bunches move slower than single steps because of narrow terraces within
- a bunch with widths smaller that the diffusion length
- 3. Step repulsions have little effect on growth rate

How can supersteps move faster than individual steps in solution growth?

# Step Repulsions can be effective in solution growth



Larger bunches have narrower terraces, and fewer impurities

Driving force independent of terrace width: All steps want to move forward except for the bottom step of a bunch

**Repulsions** from steps behind can help push first step forward past impurities

In a large bunch, the bunch is tighter and the repulsions are greater.

Supersteps self-assemble when impurities greatly impede motion of individual steps

 $l_d = 0$  A = 0.10 (small)  $\gamma = 0.5$  (moderate) Dead Zone

 $l_d = 0$  A = 0.15 (small)  $\gamma = 0.5$  (moderate) Macrostep formation

#### Velocity against driving force



#### We recover experimental trends along with superstep effect !!

## Conclusions

Impurity induced step retardation can explain both step bunching and the very fast motion of step bunches

The constant driving force independent of terrace width in solution growth is a crucial feature that allows large bunches to move together.

Repulsions are effective in helping the bunch move rapidly only when the first step is sufficiently pinned by impurities.

The new impurity model is very general and can explain existence of different regimes in different systems.

- vapor growth bunching and slow coarsening.
- solution growth dead zone and superstep formation